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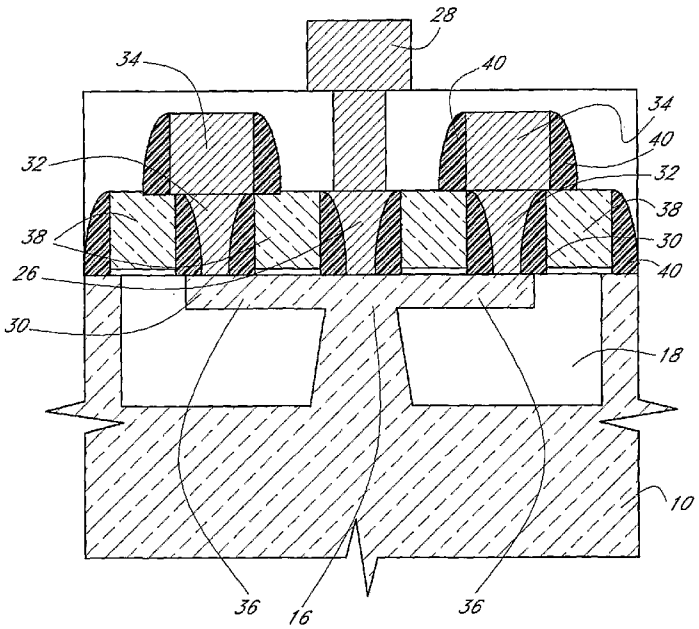
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(54) Title: CAPACITORLESS DRAM ON BULK SILICON



(57) Abstract: A method of forming capacitorless DRAM over localized silicon-on-insulator comprises the following steps: A silicon substrate (10) is provided, and an array of silicon studs (16) is defined within the silicon substrate. An insulator layer (18) is defined atop at least a portion of the silicon substrate (10), and between the silicon studs (16). A silicon-over-insulator layer (22, 24) is defined surrounding the silicon studs (16) atop the insulator layer(18), and a capacitorless DRAM (26-40) is formed within and above the silicon-over-insulator layer (22, 24).

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